Elektronische Bauelemente

2N5400

-0.6 A, -130 V

PNP Plastic Encapsulated Transistor

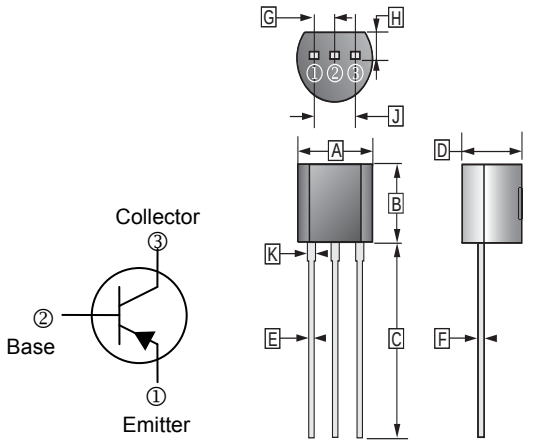
RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

FEATURES

- Switching and amplification in high voltage
- Applications such as telephony
- Low current(max.600mA)
- High voltage(max.130V)

TO-92



REF.	Millimeter	
	Min.	Max.
A	4.40	4.70
B	4.30	4.70
C	12.70	-
D	3.30	3.81
E	0.36	0.56
F	0.36	0.51
G	1.27 TYP.	
H	1.10	-
J	2.42	2.66
K	0.36	0.76

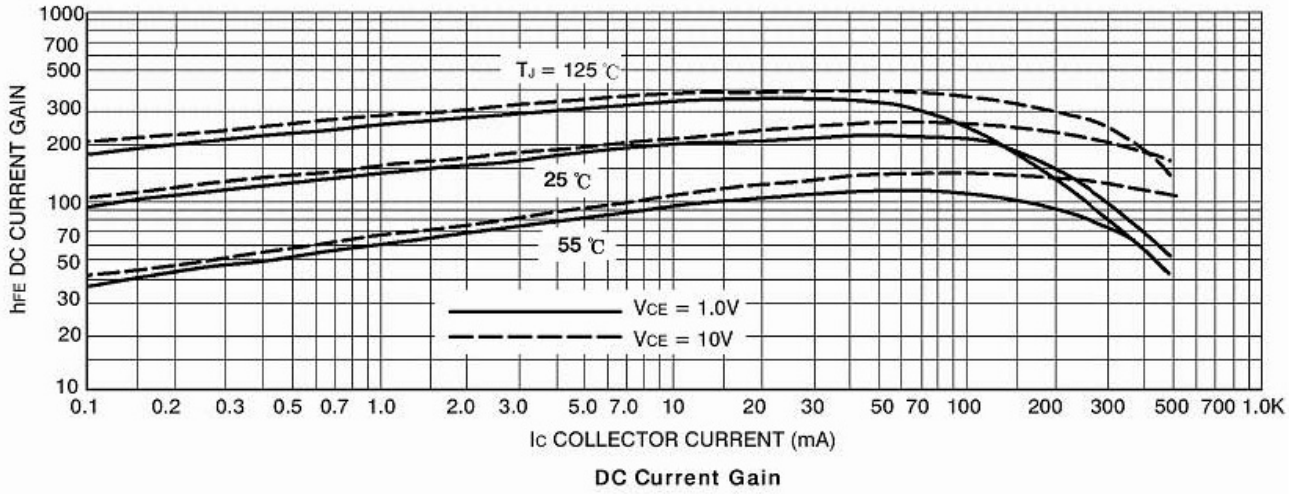
ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-130	V
Collector to Emitter Voltage	V_{CEO}	-120	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-600	mA
Collector Power Dissipation	P_C	625	mW
Junction, Storage Temperature	T_J, T_{STG}	150, -55~150	°C

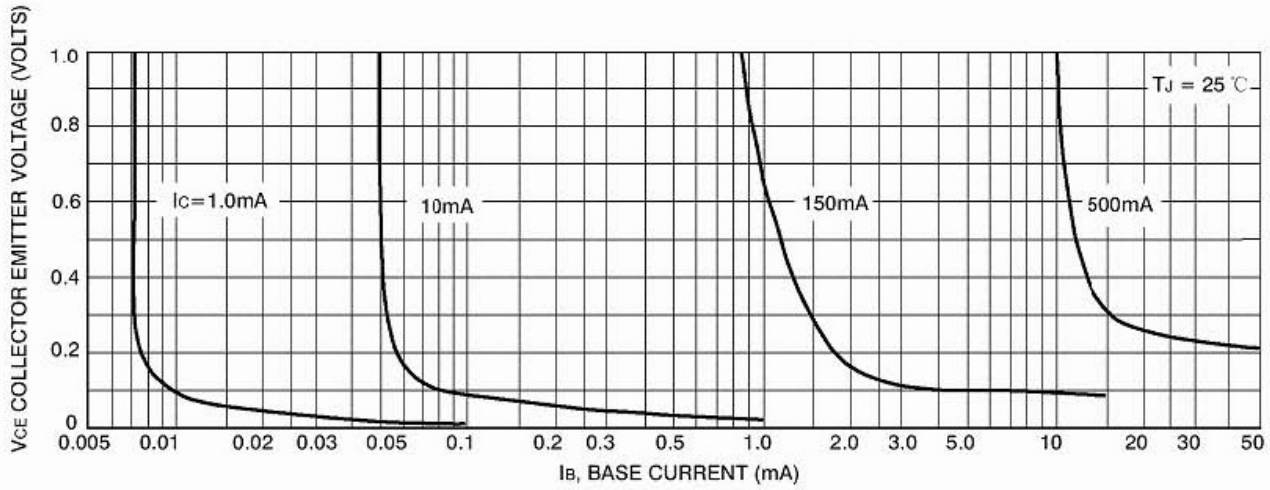
ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	-130	-	-	V	I_C=-100μA, I_E = 0A
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	-120	-	-	V	I_C=-1mA, I_B = 0A
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	-5	-	-	V	I_E=-10μA, I_C = 0A
Collector Cut-Off Current	I_{CBO}	-	-	-0.1	μA	V_{CB}=-100V, I_E = 0 A
Emitter Cut-Off Current	I_{EBO}	-	-	-0.1	μA	V_{EB}=-3V, I_C =0 mA
DC Current Gain	h_{FE1}	30	-	-		V_{CE}=-5V, I_C=-1mA
	h_{FE2}	40	-	180		V_{CE}=-5V, I_C=-10mA
	h_{FE3}	40	-	-		V_{CE}=-5V, I_C=-50mA
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	--	-	-0.2	V	I_C=-10mA, I_B=-1mA
		--	-	-0.5	V	I_C=-50mA, I_B=-5mA
Base to Emitter Voltage	$V_{BE(sat)}$	--	-	-1	V	I_C=-10mA, I_B=-1mA
		--	-	-1	V	I_C=-50mA, I_B=-5mA
Collector Output Capacitance	C_{ob}	-	-	6	pF	V_{CB} = -10V, I_E = 0A, f=1MHz
Transition Frequency	f_T	100	-	-	MHz	V_{CE} = -10V, I_C = -10mA, f=30MHz

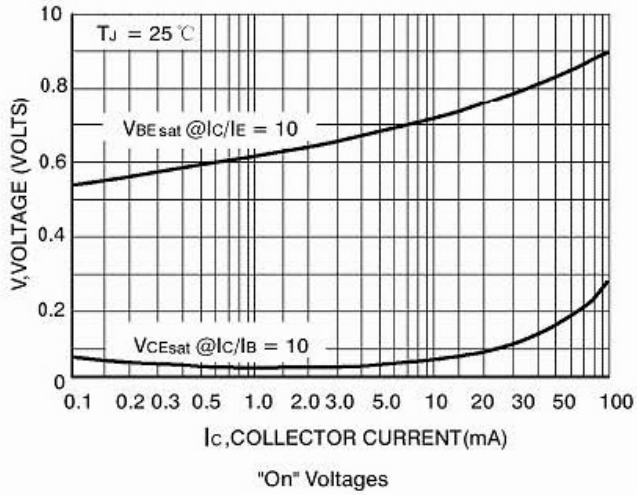
CHARACTERISTIC CURVES



DC Current Gain



Collector Saturation Region



"On" Voltages